VS-HFA04SD60SHM3

Vishay Semiconductors

HEXFRED[®], Ultrafast Soft Recovery Diode, 4 A



www.vishay.com

D-PAK (T	O-252AA
----------	---------

	○ 2, 4 ▲
0 1	0 3
N/C	Anode

PRODUCT SUMMARY					
Package	TO-252AA (D-PAK)				
I _{F(AV)}	4 A				
V _R	600 V				
V _F at I _F	1.8 V				
t _{rr} typ.	17 ns				
T _J max.	150 °C				
Diode variation	Single die				

FEATURES

- Ultrafast recovery time
- Ultrasoft recovery
 Very low I_{RRM}
- Very low I_{RR}
 Very low Q_{rr}
- Guaranteed avalanche
- Specified at operating temperature
- AEC-Q101 gualified
- Meets JESD 201 class 2 whisker test
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION/APPLICATIONS

These diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for freewheeling, flyback, power converters, motor drives, and other applications where high speed and reduced switching losses are design requirements.

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Cathode to anode voltage	V _{RRM}		600	V
Maximum continuous forward current	I _{F(AV)}	T _C = 100 °C	4	
Single pulse forward current	I _{FSM}		25	A
Repetitive peak forward current	I _{FRM}	T _C = 116 °C	16	
Maximum power dissipation	PD	T _C = 100 °C	10	W
Operating junction and storage temperatures	T _J , T _{Stg}		- 55 to 150	°C

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	-	
		$I_F = 4 A$	-	1.5	1.8	V
Forward voltage See fig. 1	V _F	I _F = 8 A	-	1.8	2.2	
See lig. 1		I _F = 4 A, T _J = 125 °C	-	1.4	1.7	
Maximum reverse		$V_{R} = V_{R}$ rated	-	0.17	3.0	
leakage current	IR	$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$	-	44	300	μA
Junction capacitance	CT	V _R = 200 V	-	4	8	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH

Revision: 21-Aug-13

1

Document Number: 94756

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



RoHS

COMPLIANT

www.vishay.com

ISHAY

VS-HFA04SD60SHM3

Vishay Semiconductors

DYNAMIC RECOVERY CHARACTERISTICS ($T_C = 25$ °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS	
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t =$	200 A/µA, V _R = 30 V	-	17	-		
Reverse recovery time	t _{rr}	T _J = 25 °C		-	28	42	ns	
		T _J = 125 °C		-	38	57		
Deels receivers a unreet	I _{RRM}	T _J = 25 °C		-	2.9	5.2	•	
Peak recovery current		IRRM	T _J = 125 °C	I _F = 4 A dI _F /dt = 200 A/μs	-	3.7	6.7	A
	Q _{rr}	T _J = 25 °C	$V_{\rm R} = 200 \text{ V}$	-	40	60	nC	
Reverse recovery charge		Qrr	T _J = 125 °C		-	70	105	
		T _J = 25 °C		-	280	-	A // 10	
Rate of fall of recovery current	dl _{(rec)M} /dt	T _J = 125 °C		-	235	-	A∕µs	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		- 55	-	150	°C
Thermal resistance, junction to case	R _{thJC}		-	-	5.0	°C/W
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	0/11
Weight			-	2.0	-	g
weight			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style D-PAK		HFA04	SD60SH	

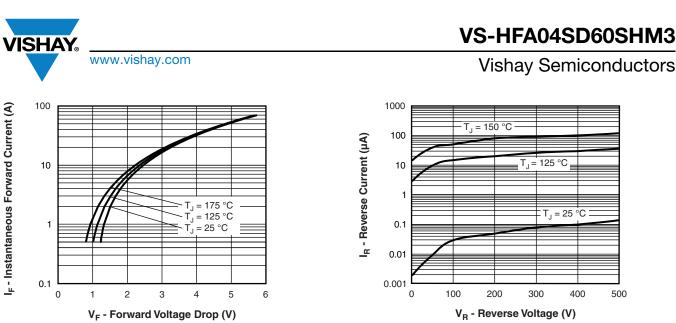


Fig. 1 - Typical Forward Voltage Drop Characteristics

Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

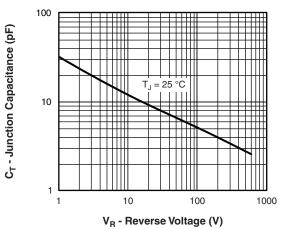
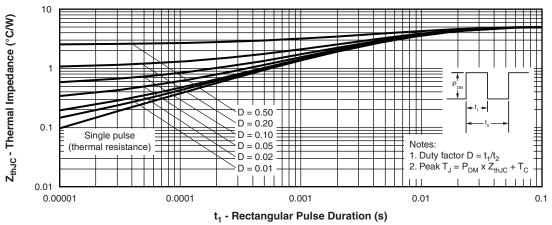
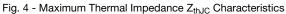


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage





For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



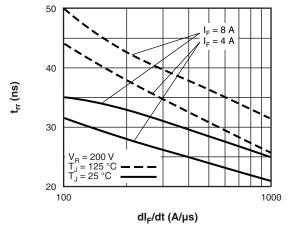
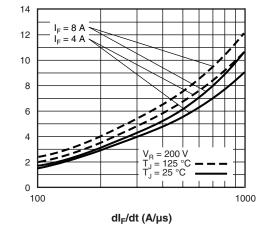


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

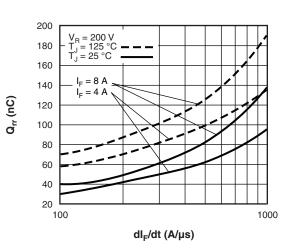


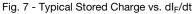
I_{RR} (A)

Fig. 6 - Typical Recovery Current vs. dl_F/dt

VS-HFA04SD60SHM3

Vishay Semiconductors





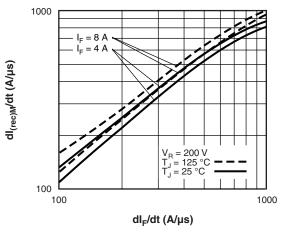


Fig. 8 - Typical dI_{(rec)M}/dt vs. dI_F/dt

Revision: 21-Aug-13 **4** Document Number: 94756 For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

VS-HFA04SD60SHM3



Vishay Semiconductors

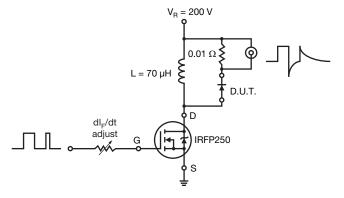
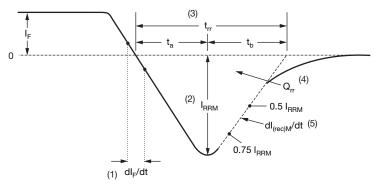


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dI_F/dt rate of change of current through zero crossing
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (5) dl_{(rec)M}/dt peak rate of change of current during t_b portion of t_{rr}

 $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$

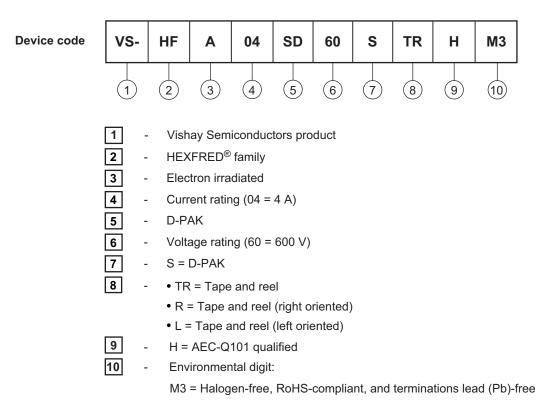
Fig. 10 - Reverse Recovery Waveform and Definitions



Vishay Semiconductors

ORDERING INFORMATION TABLE

www.vishay.com



ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-HFA04SD60SHM3	75	3000	Antistatic plastic tube		
VS-HFA04SD60STRHM3	2000	2000	13" diameter reel		
VS-HFA04SD60STRRHM3	3000	3000	13" diameter reel		
VS-HFA04SD60STRLHM3	3000	3000	13" diameter reel		

LINKS TO RELATED DOCUMENTS				
Dimensions www.vishay.com/doc?95519				
Part marking information	www.vishay.com/doc?95518			
Packaging information	www.vishay.com/doc?95033			

Document Number: 94756



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Material Category Policy

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.